

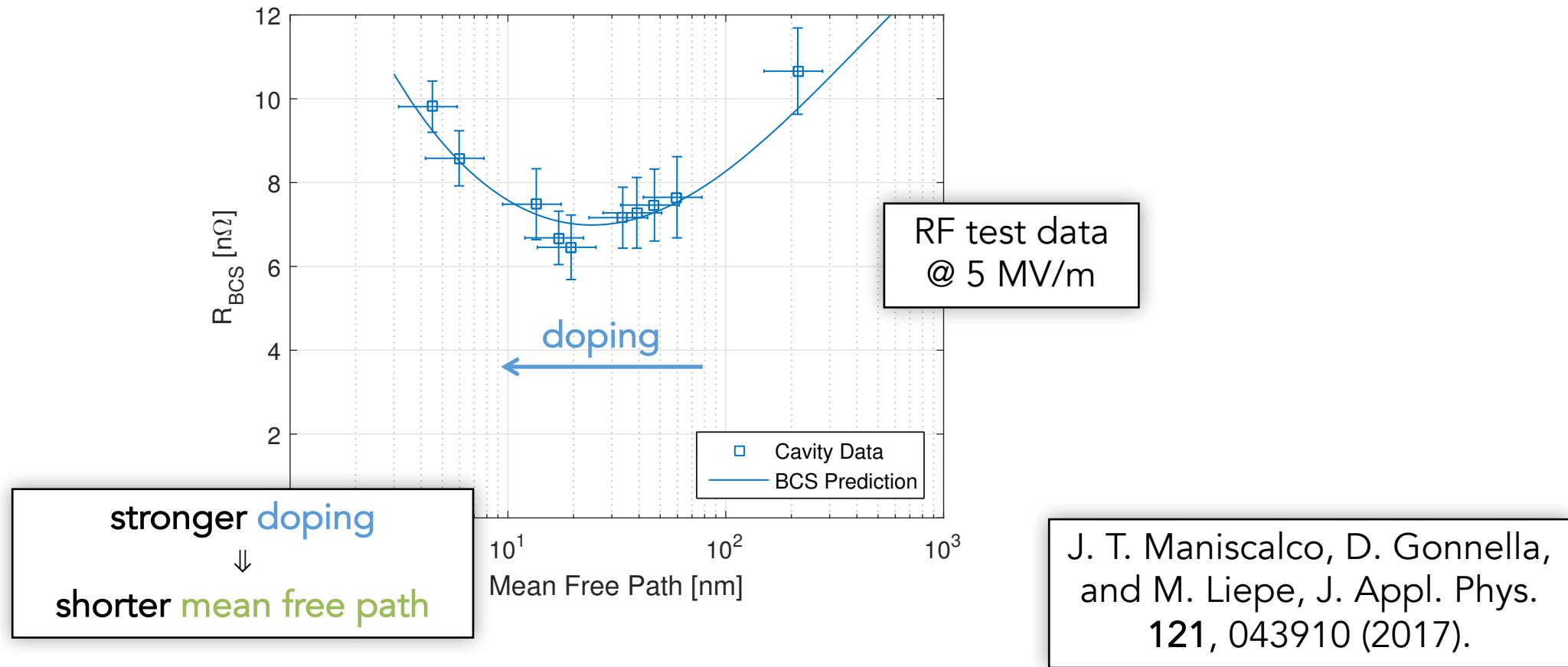


Analysis of Mean Free Path and Field- Dependent Surface Resistance

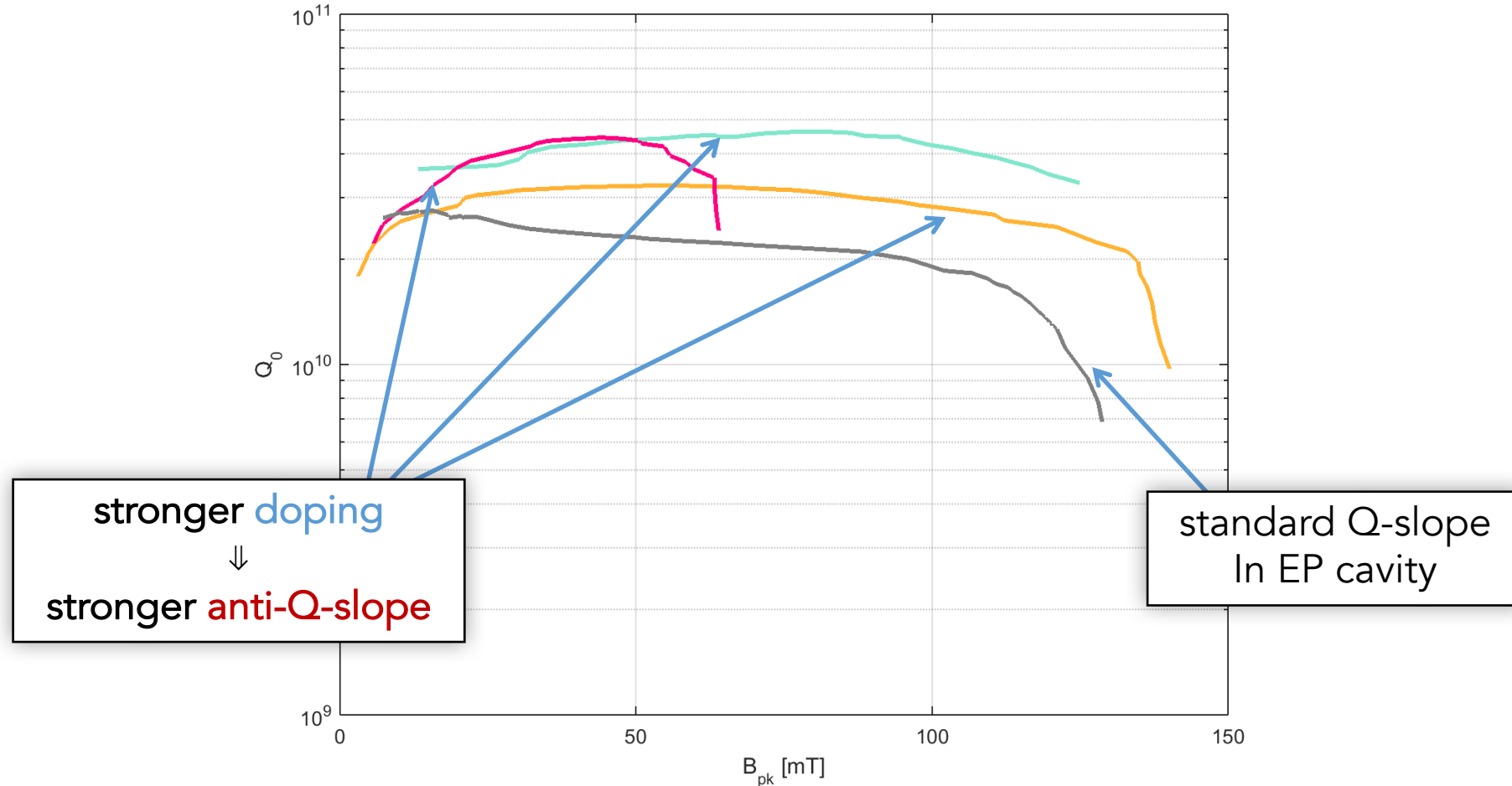
James T. Maniscalco
November 15, 2017
TTC Topical Workshop



- Classic observation:
 - Dope niobium, reach minimum in R_{BCS} vs. mean free path



- “New” observation:
 - Dope niobium, see “anti-Q-slope”





Impurity-Doping Observations

- Most study of AQS has been phenomenological
 - Project-driven field – optimizing recipes, etc.
- Growing number of theoretical models





Background: Gurevich Theory

- Nonequilibrium superconductivity +
- Electron DOS modified by screening currents +
- Quasiparticle overheating

- New contribution: **qp overheating** \propto **mean free path**

A. Gurevich, Phys. Rev.
Lett. **113**, 087001 (2014).



- Quasiparticle **overheating**

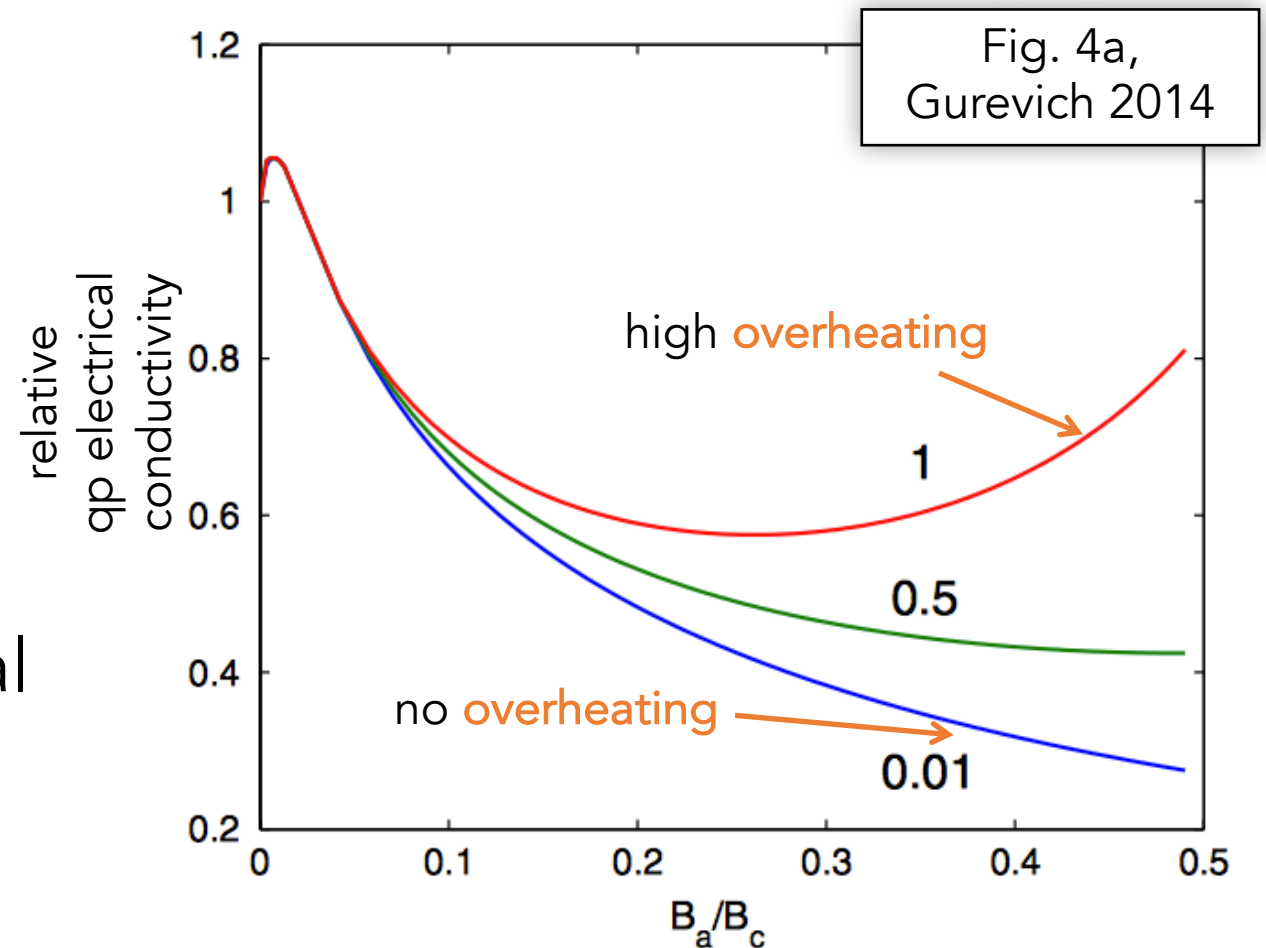
$$T - T_0 = \alpha' \frac{1}{2} H_a^2 R_{\text{BCS}}(H_a, T) = \alpha' \frac{P_{\text{diss}}}{\text{area}}$$

$$\alpha' = \left(\frac{1}{Y} + \frac{d}{\kappa} + \frac{1}{h_K} \right)$$

Y (e-phonon energy transfer)
dominates, can be
dependent on
mean free path

properties of
bulk, do not
change
with doping

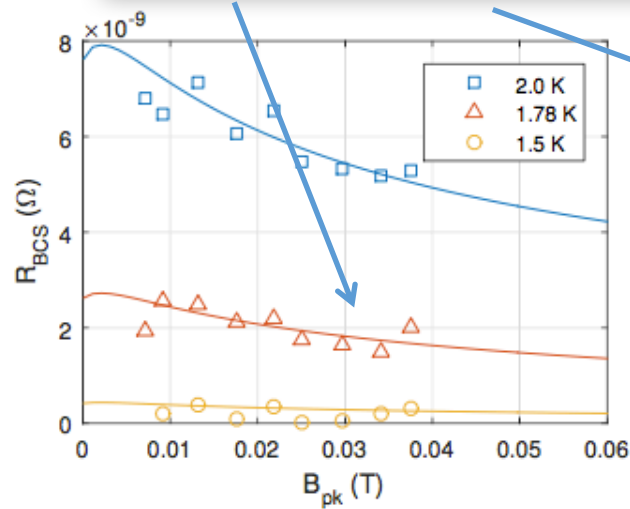
- Magnitude of R_{BCS} reduction controlled ("tuned") by **quasiparticle overheating**
- Overheating parameter α is theory's **only free parameter** (*i.e.* not controlled by material properties)



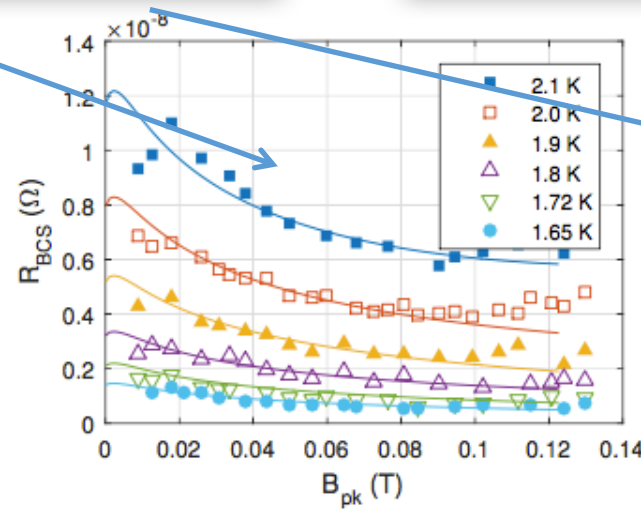
- CW RF tests, 1.3 GHz TESLA single-cells, **N-doped**
- Fit Gurevich theory to experimental data
 - α' as free fitting parameter, **mfp** from RF fitting

Increasing **mean free path**,
increasing α'

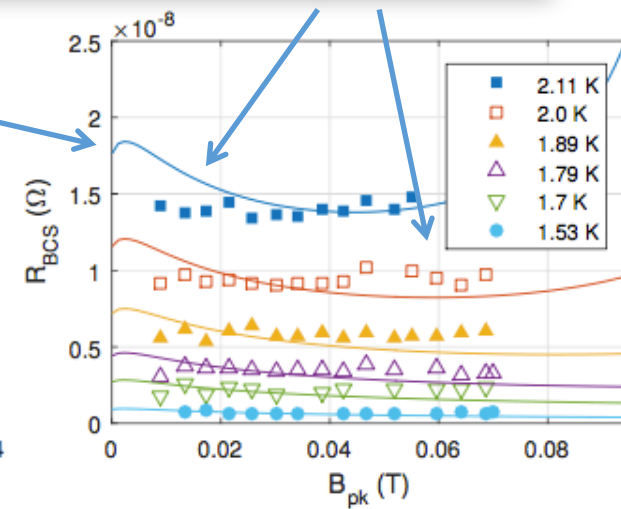
Theory needs expansion to
predict outside **dirty limit**



mfp = 4.5 nm
 α' = 2.1 mK m²/W

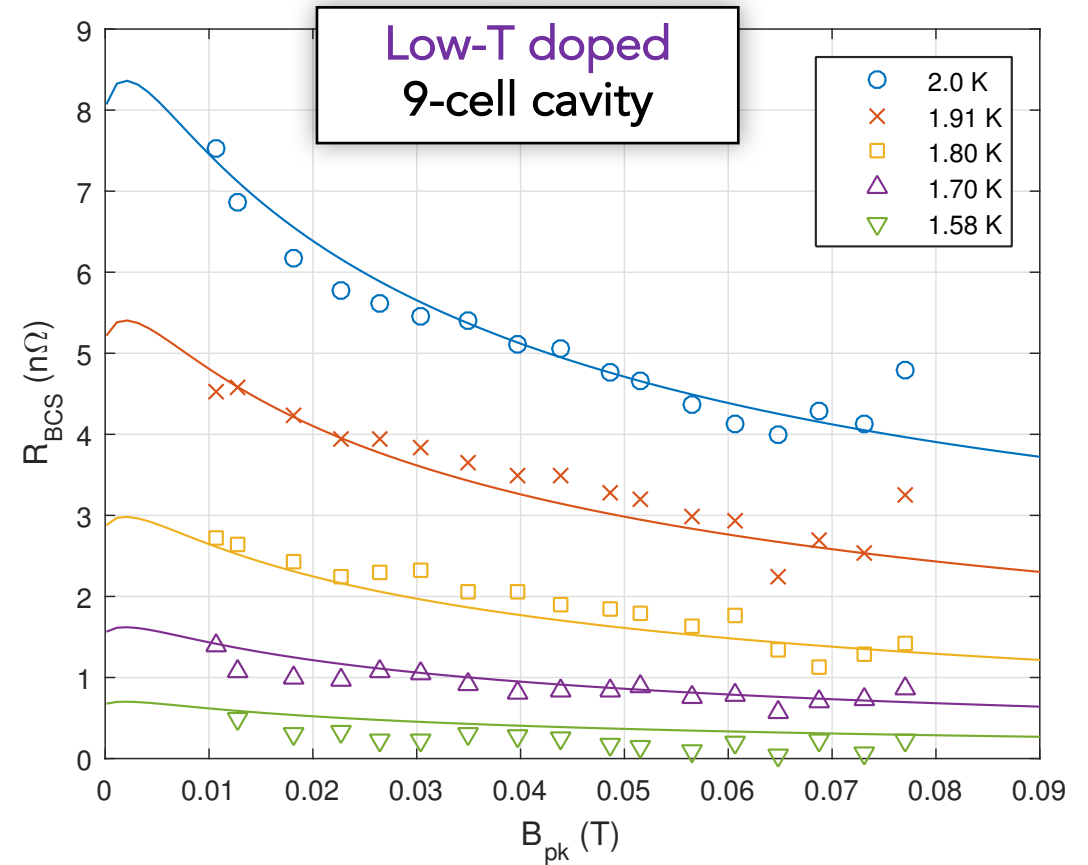
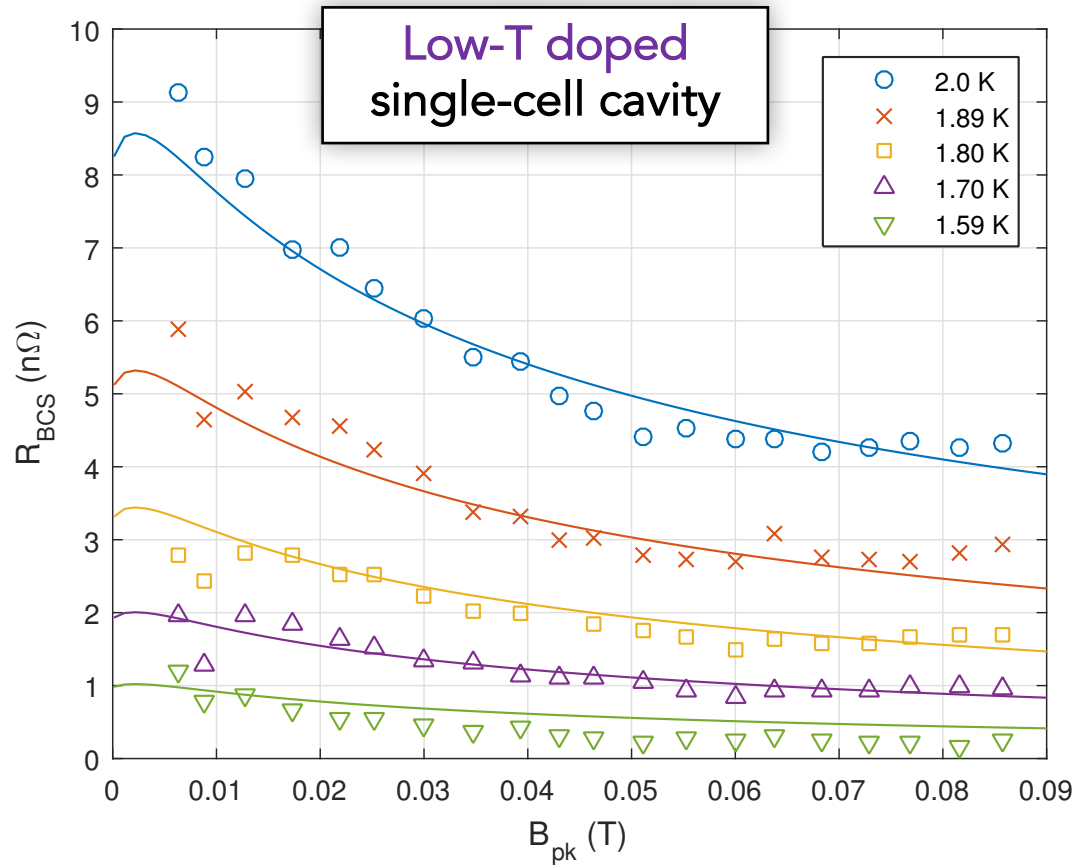


mfp = 34 nm
 α' = 7.0 mK m²/W

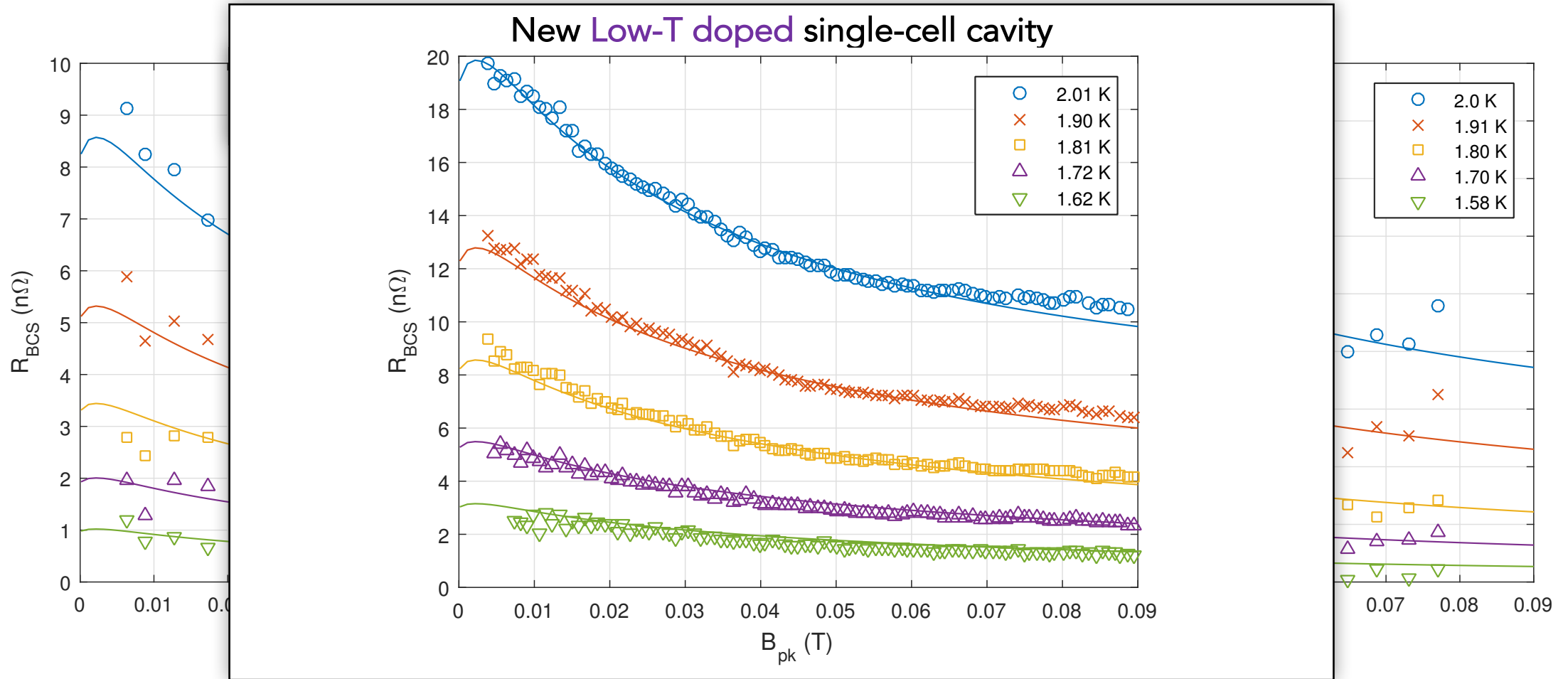


mfp = 213 nm
 α' = 17 mK m²/W

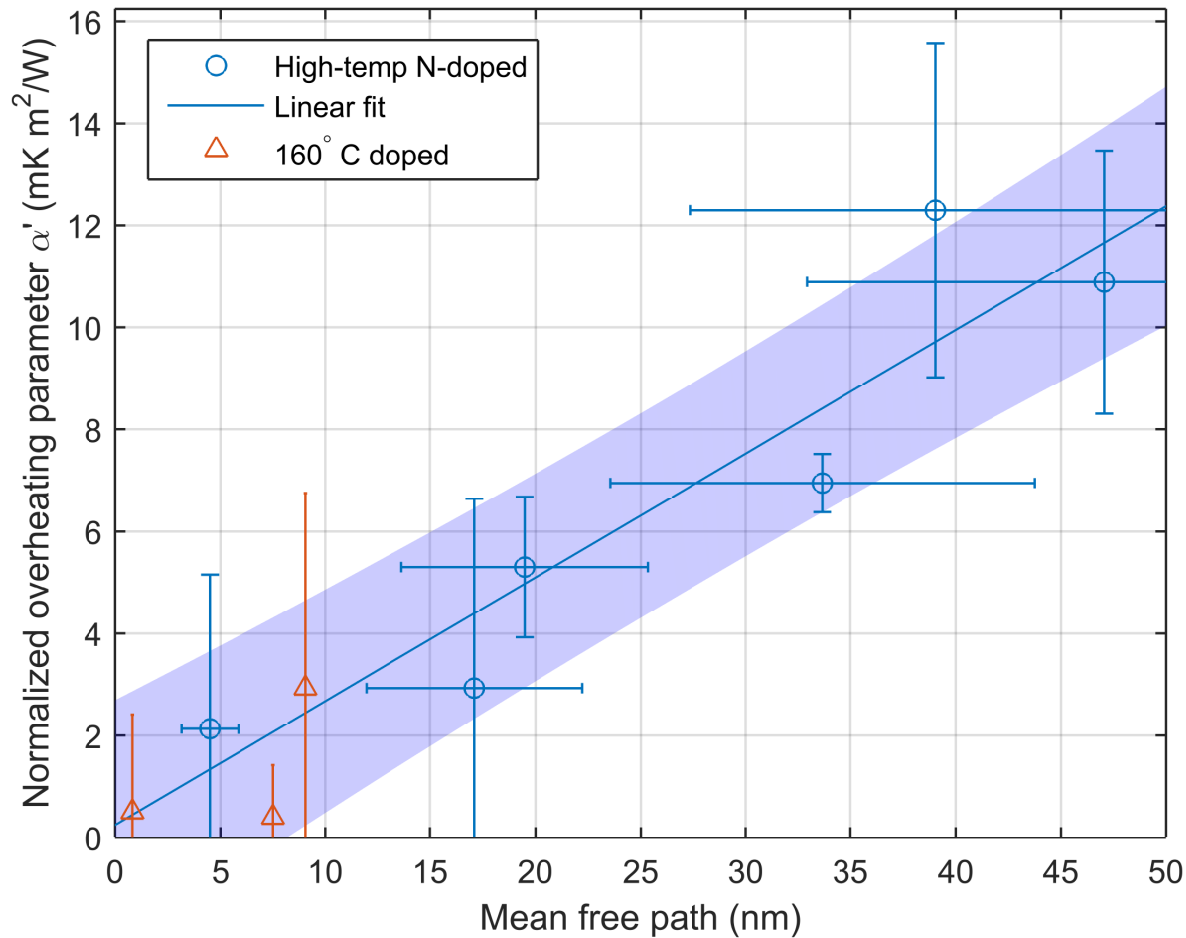
- CW RF tests, 1.3 GHz TESLA single-cells, **Low-T-doped**



- CW RF tests, 1.3 GHz TESLA single-cells, **Low-T-doped**

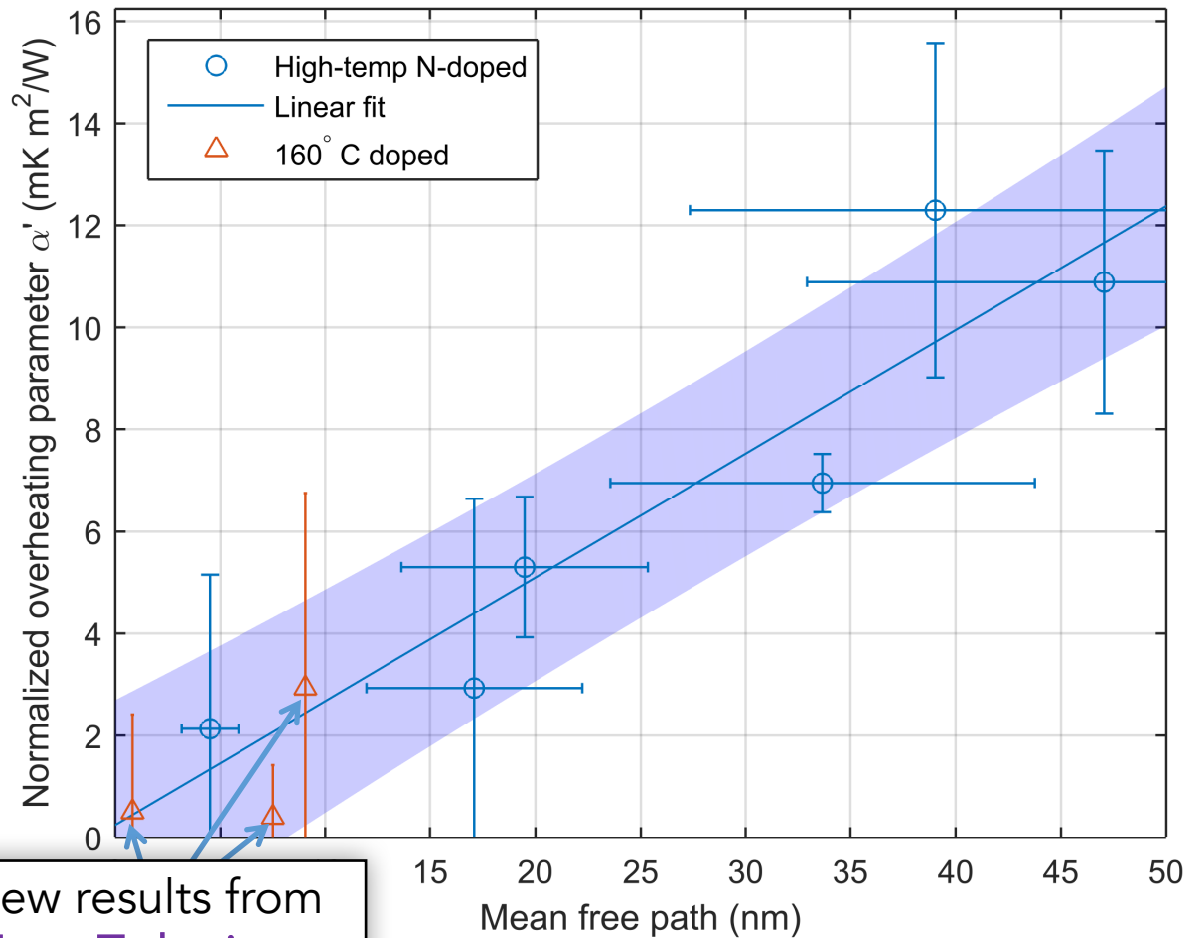


- Linear dependence of α' on mean free path (impurity content)



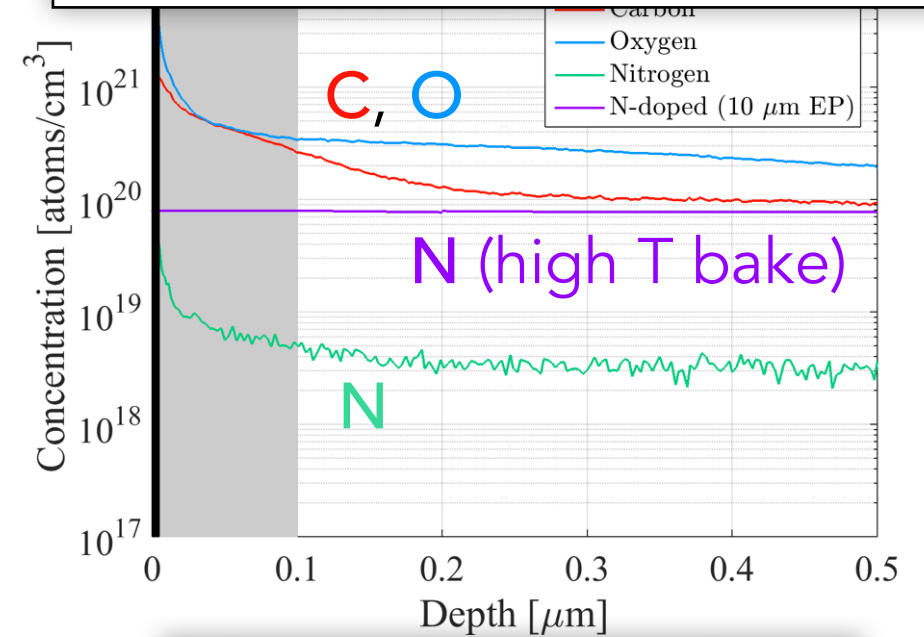
J. T. Maniscalco, D. Gonnella,
and M. Liepe, *J. Appl. Phys.*
121, 043910 (2017).

- Linear dependence of α' on mean free path (impurity content)



New results from Low-T doping

Agreement remarkable due to **drastic differences** in RF penetration layer!
 Not clear that nitrogen is still the culprit



P. N. Koufalis, D. L. Hall, M. Liepe, and J. T. Maniscalco, arXiv:1612.08291 (2016).

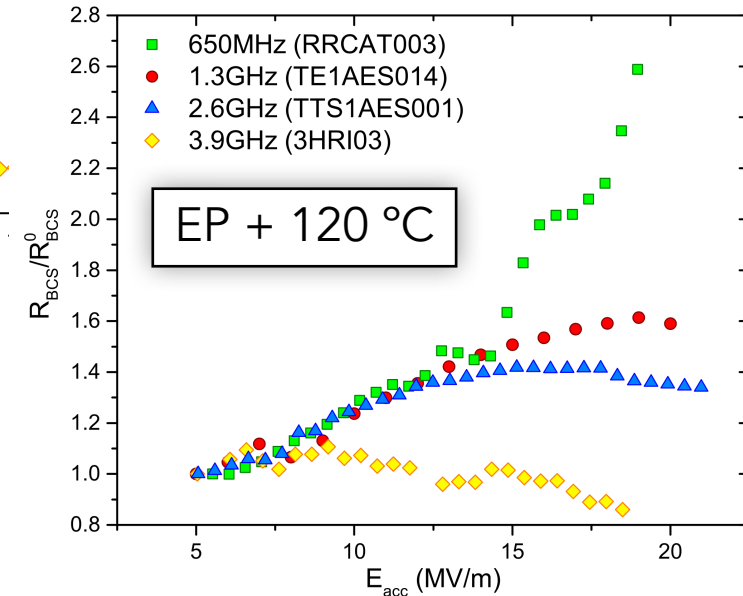
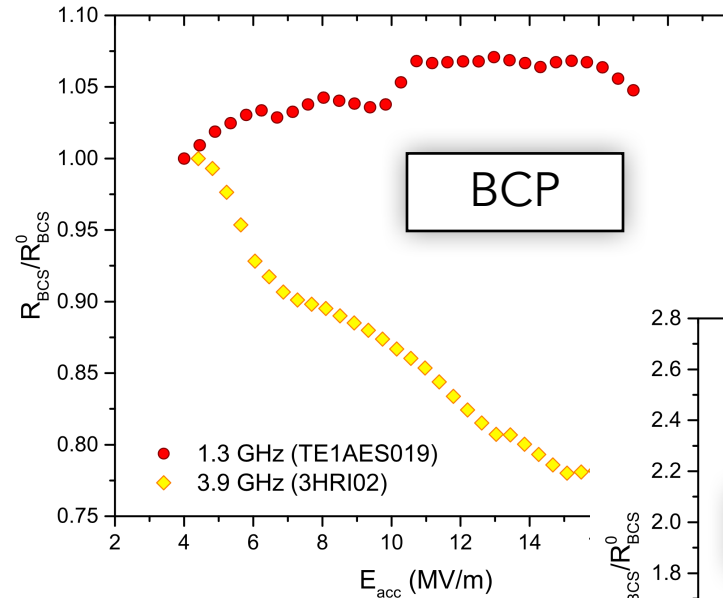
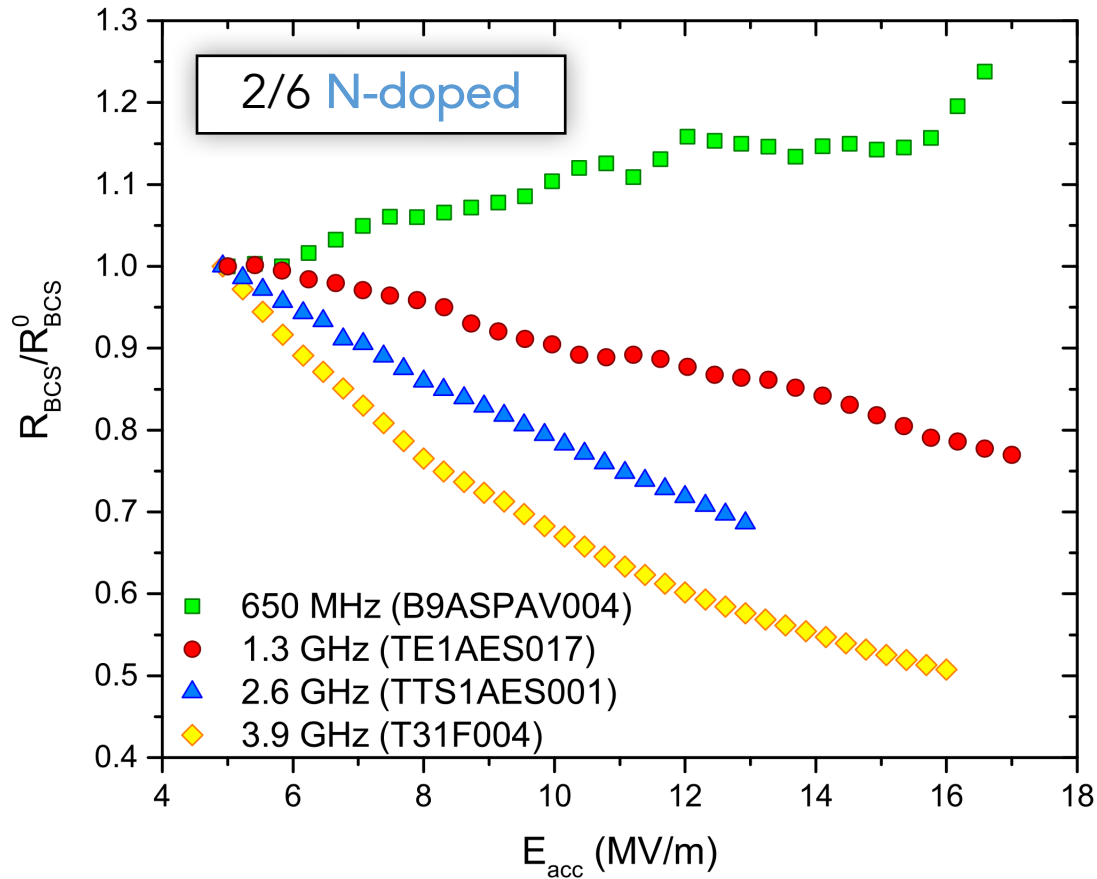


Limitations & Open Questions

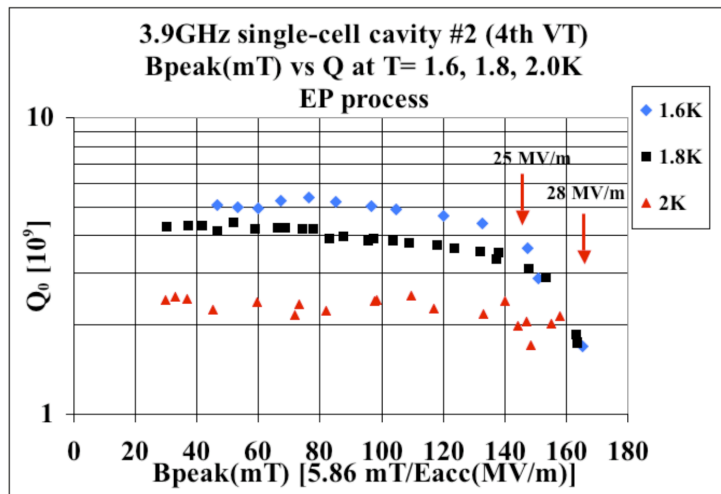
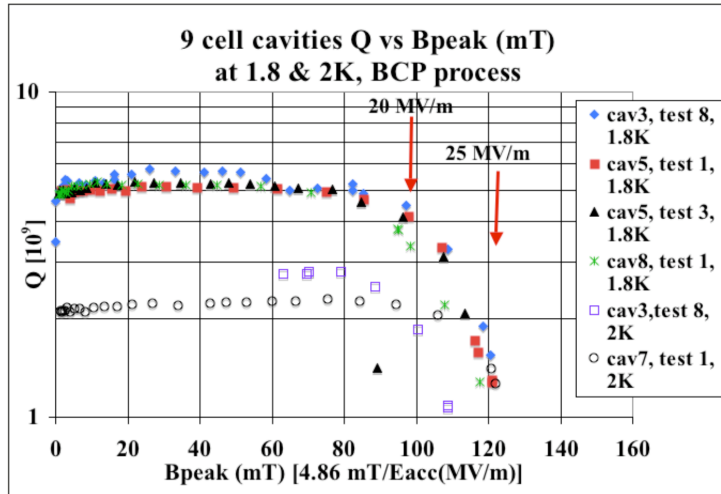
- Very high α' yields results not (yet) observed in the lab
 - Linear approximation – is there a more appropriate form?
- Theory does not extend to clean niobium
 - Limited to $mfp < 100$ nm
 - Same problem as above? Long mfp gives high α' ...
- How successful is the model at other frequencies?
 - High frequency SRF is a hot topic!
 - Lower construction costs, new optima of ω and T for new surfaces...



- New results from FNAL
 - Martinello *et al.* 2017 (arXiv: 1707.07582)



- BCP and EP + 120 °C: at odds with previous results?



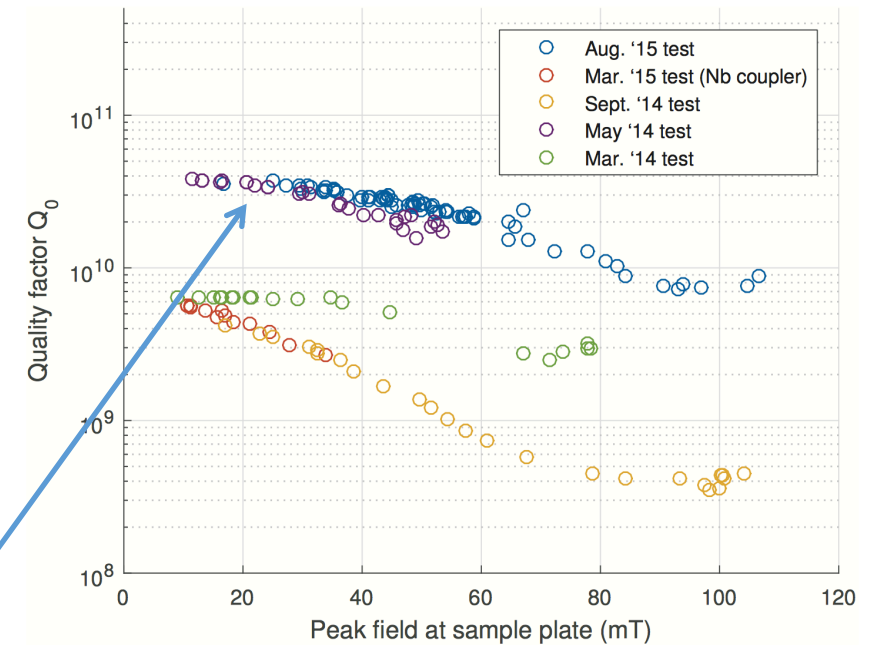
Edwards et al. (FNAL) SRF 2009

BCP @ 3.9 GHz

EP + 120 °C @ 3.9 GHz

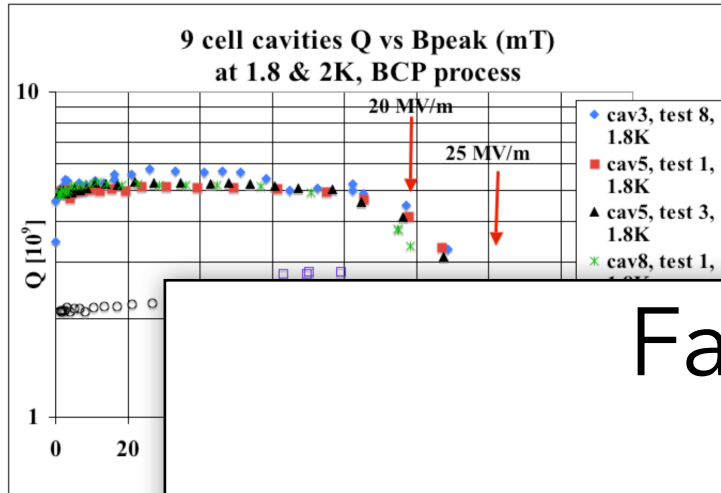
Maniscalco et al. SRF 2015

EP + 120 °C @ 3.9 GHz



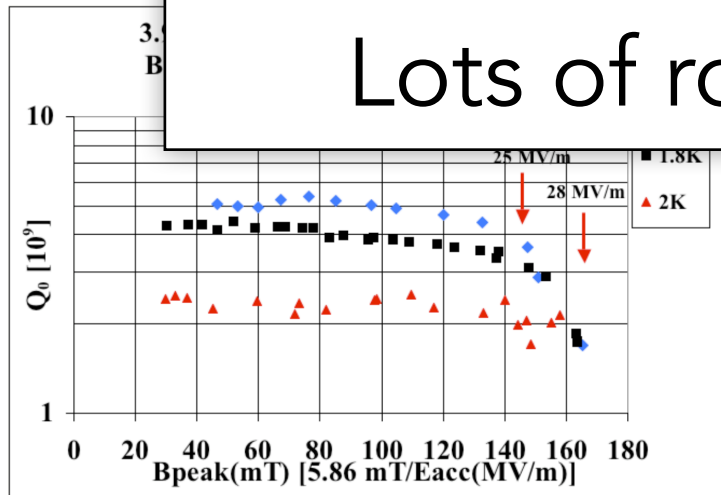
Doping High-Frequency Cavities

- BCP and EP + 120 °C: at odds with previous results?

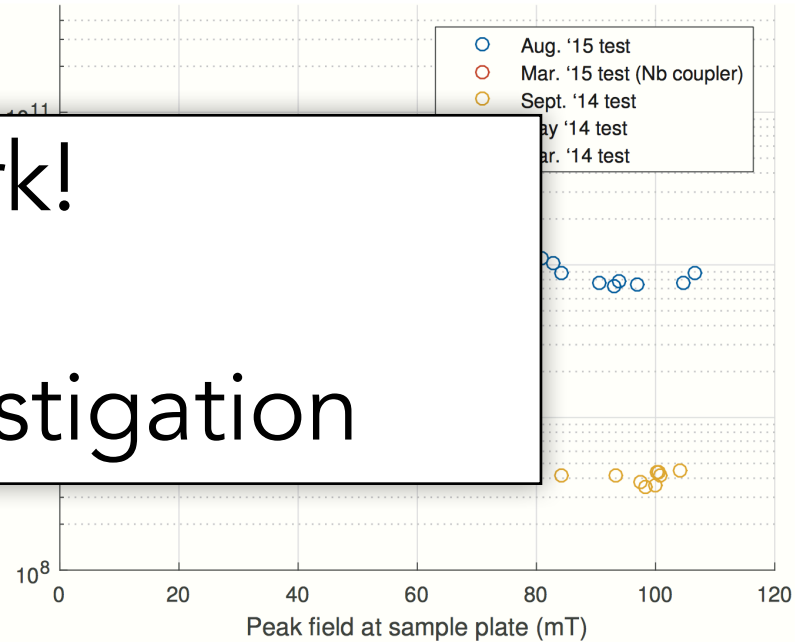


Edwards et al. (FNAL)
SRF 2009

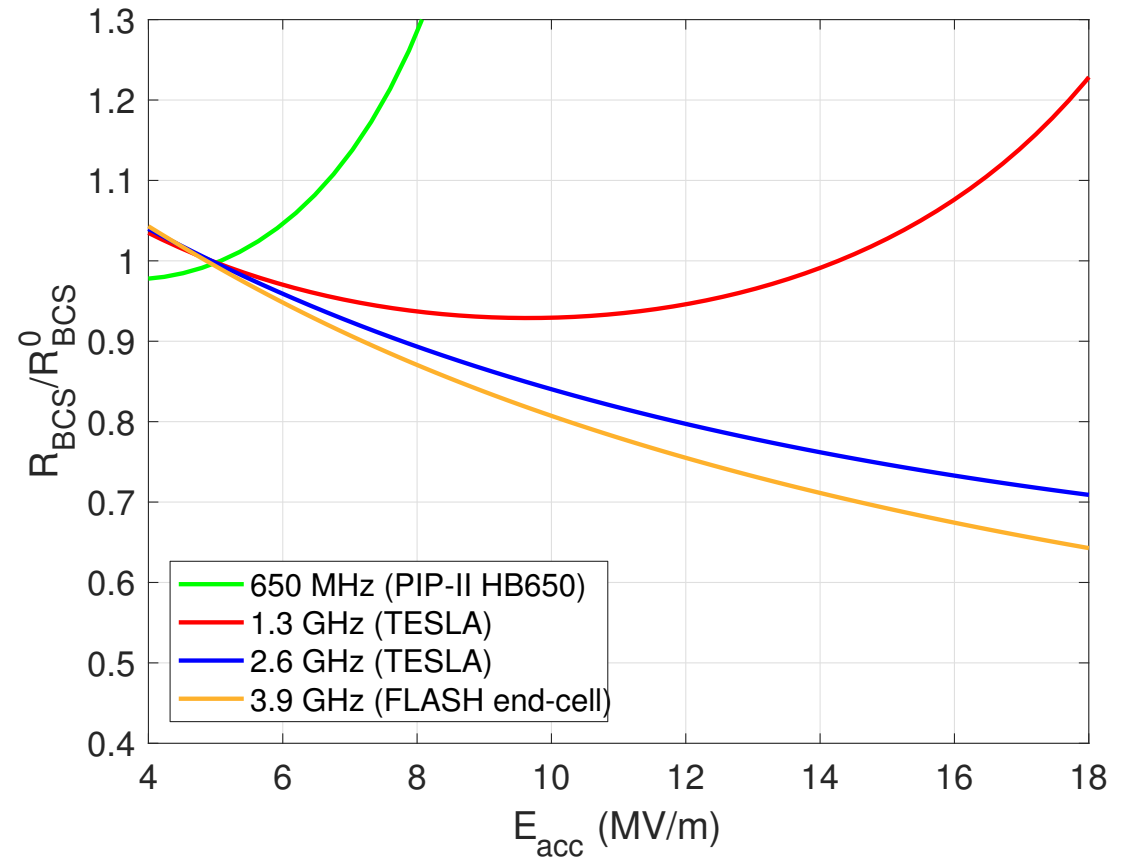
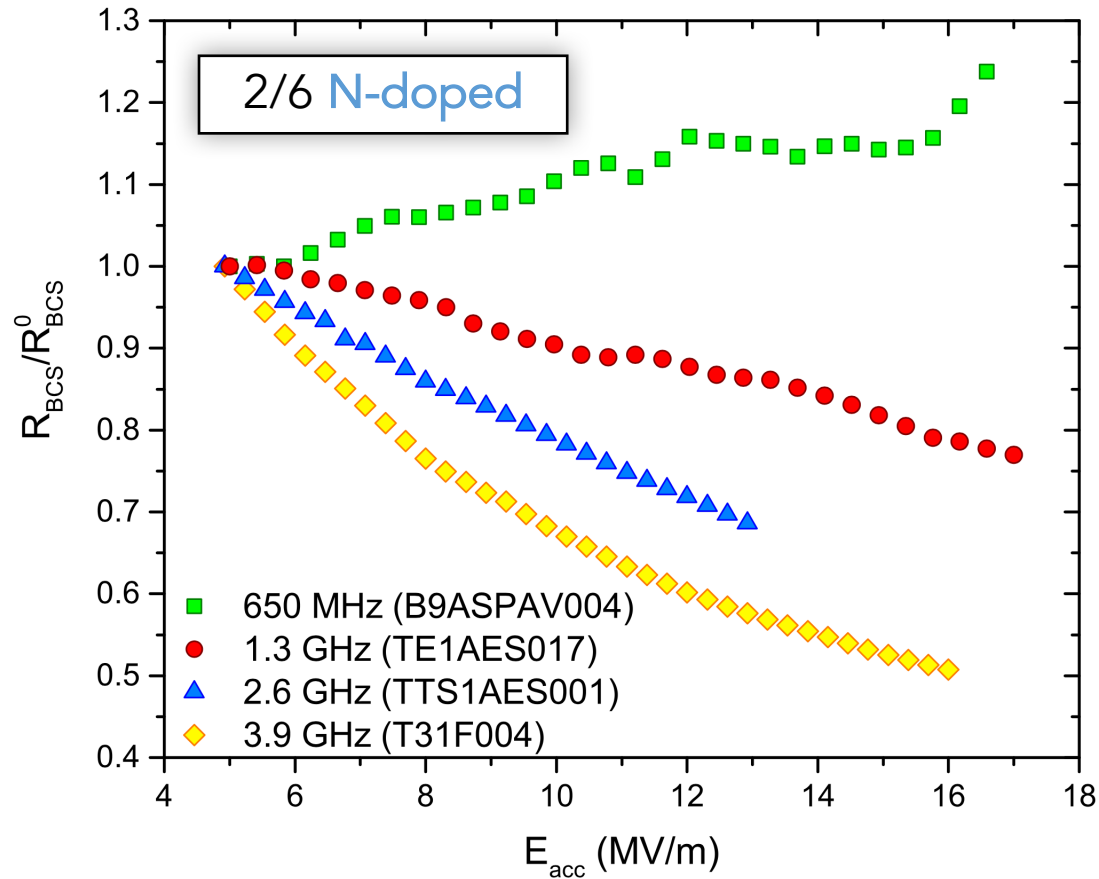
Fascinating new work!
Lots of room for more investigation



SRF 2015
EP + 120 °C
@ 3.9 GHz

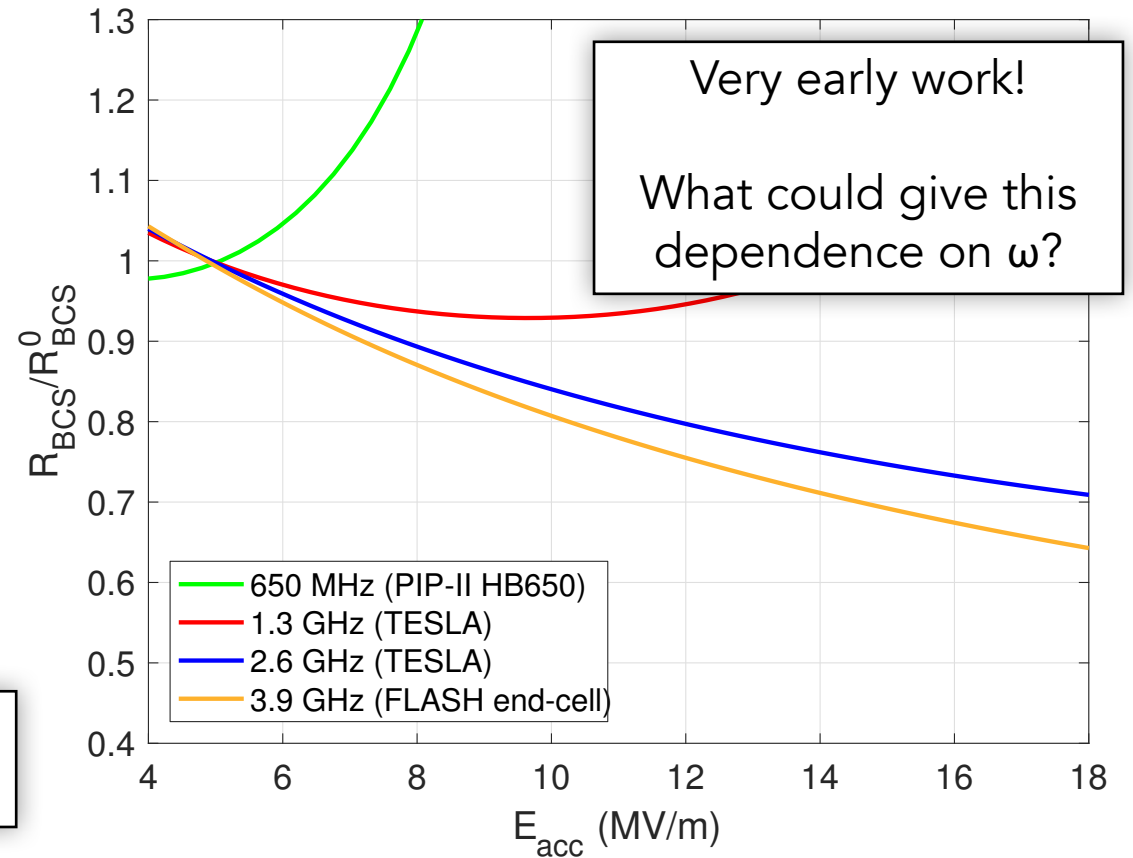
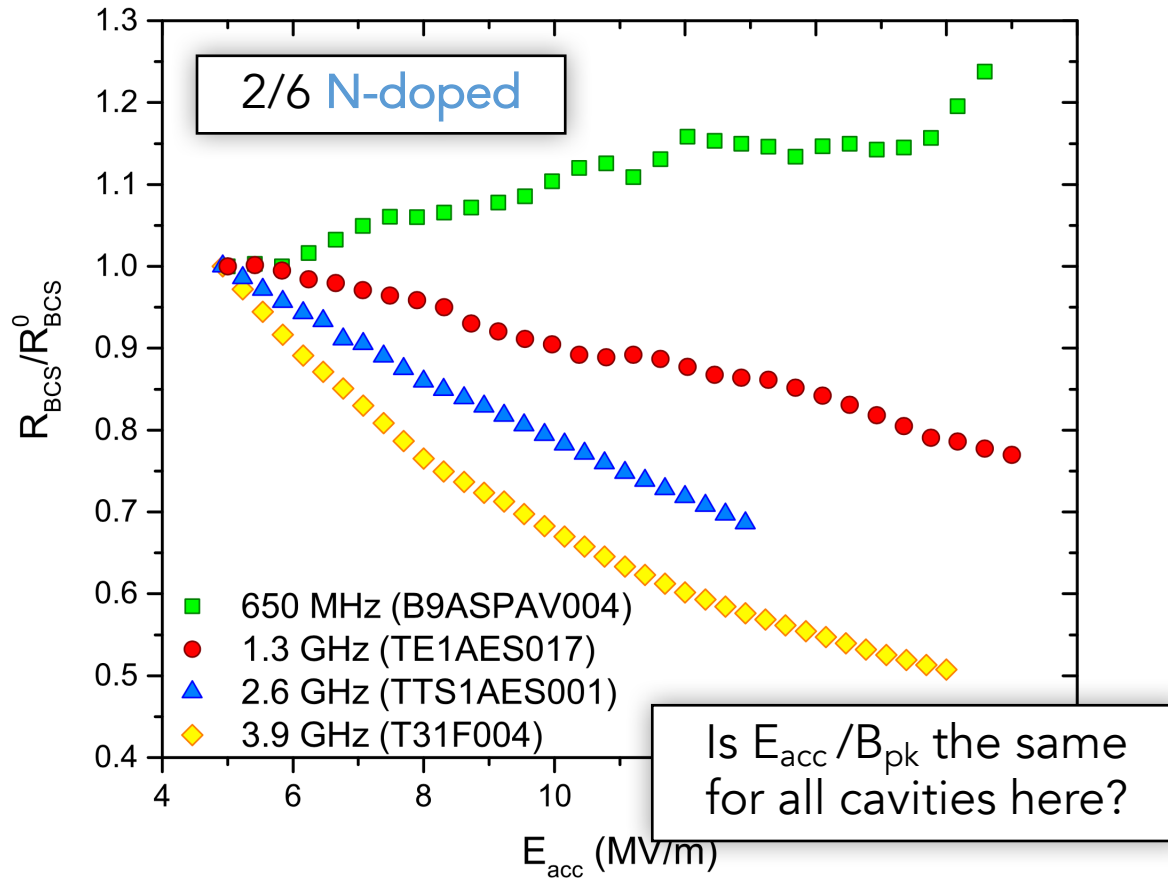


- How does our model hold up against new N-doping results?
 - Introduce an inverse dependence of α' on frequency (in this case ω^{-4}):



Doping High-Frequency Cavities

- How does our model hold up against new N-doping results?
 - Introduce an inverse dependence of α' on frequency (in this case ω^{-4}):

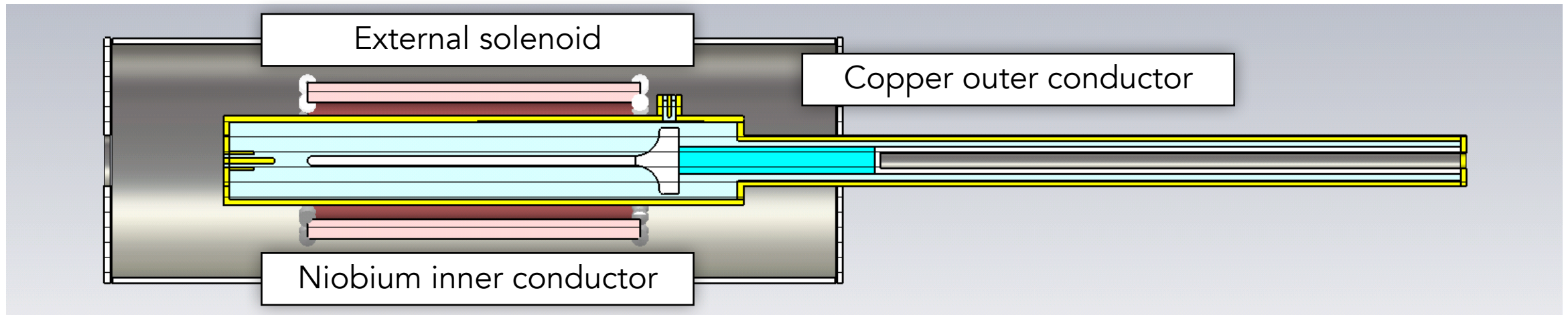




- Could this be the transition from equilibrium to nonequilibrium superconductivity?
 - Very lucky to have 1.3 GHz precisely at threshold!
 - Requires that τ_s (qp scattering time) is **between 0.12 and 0.24 ns**
 - Literature suggests longer times (**0.30-0.70 ns**), increasing with film thickness
 - Maybe cavity tests are *always* in nonequilibrium regime (as Gurevich suggests)
 - Requires that impurities drastically **increase** this characteristic time
 - No AQS (or very little) for clean cavities at 3.9 GHz
 - Literature suggests this time scale **decreases** as material gets dirtier
 - Requires that clean-limit τ_s is very short, **< 0.04 ns**



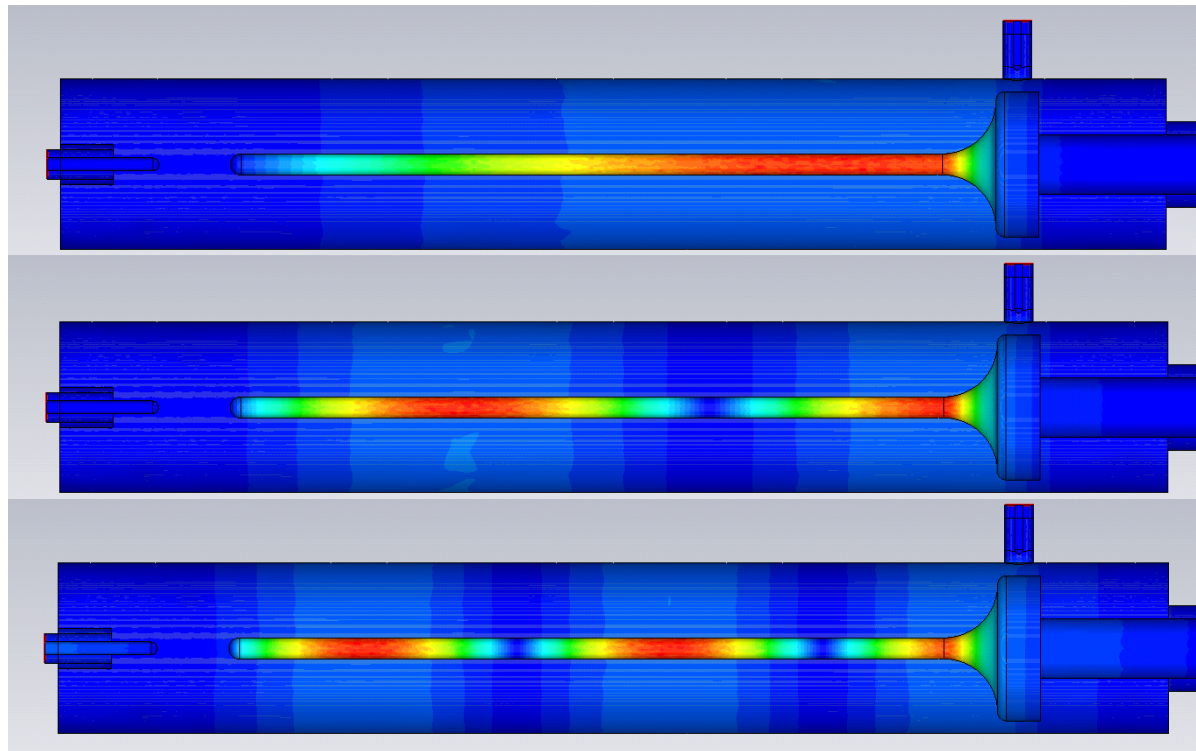
- New apparatus in the works to test frequency dependence
 - Probing “simpler” physics of DC magnetic field superimposed on weak RF field



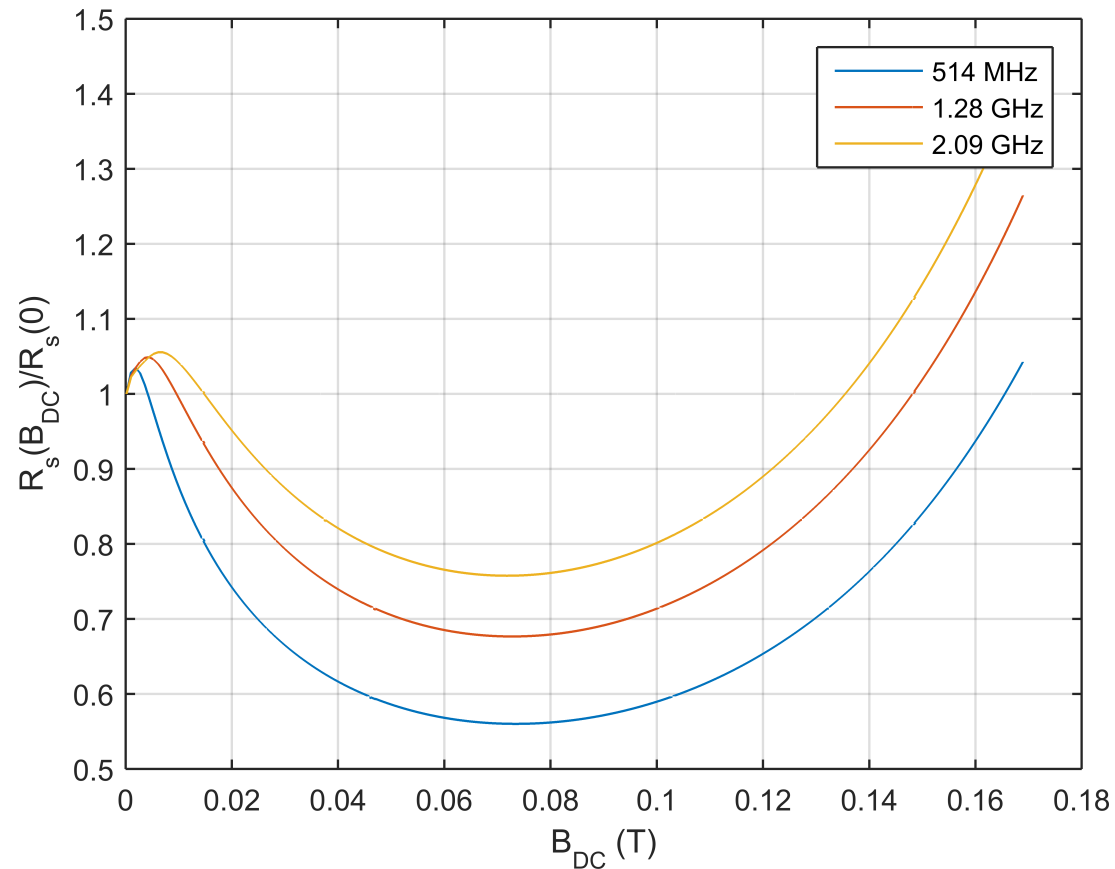
- Test for DOS smearing (DC anti-Q-slope) vs. nonequilibrium transition (no DC anti-Q-slope)
- Weak RF field → no **qp overheating**

J. T. Maniscalco, M. Liepe,
R. D. Porter, SRF 2017.

- Calorimetric measurements to extract R_s
 - Expect sensitivity between $\pm 2\%$ and $\pm 15\%$ depending on T , ω , P_{in}
- Three frequencies: ~ 500 MHz, ~ 1.3 GHz, ~ 2.1 GHz



- Expected measurements (by Gurevich theory):
 - Generally, **higher T** and **lower ω** have **larger relative decrease in R_s**





- Some requests for my fellow scientists...
 - Please show R vs. B, not R vs. E – magnetic field is the important one!
 - If you don't, please show B_{pk} / E_{acc} !
 - Please list material parameters (mfp , Δ , λ , ξ , T_c , ...) so models can be tested against experimental data
 - Keep on discovering!





- References / further reading:

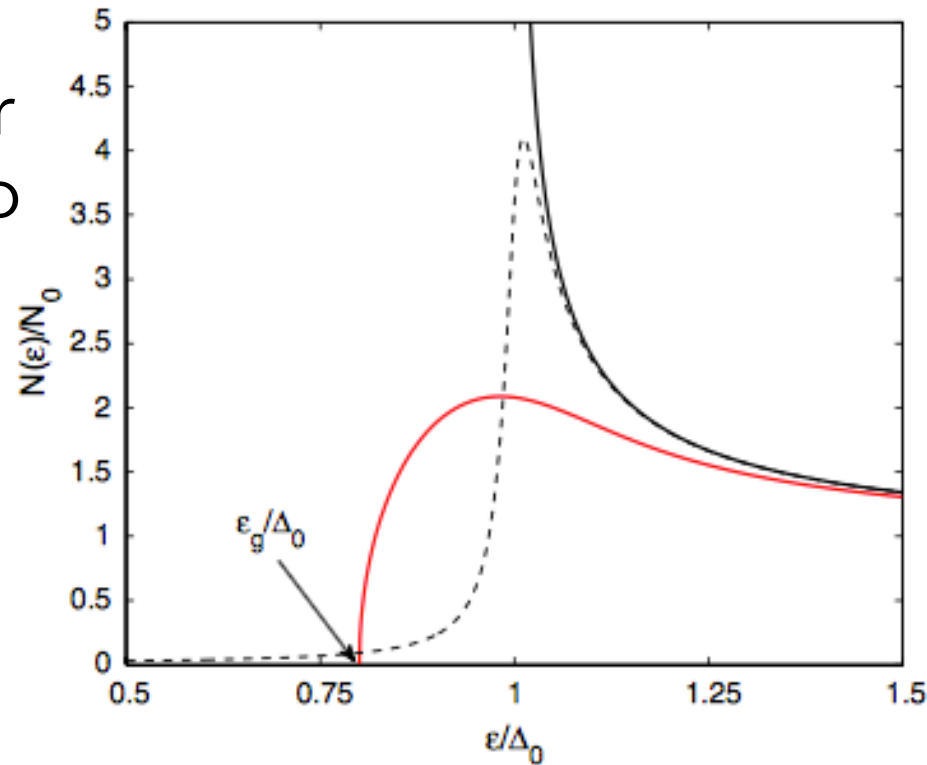
- J. T. Maniscalco, D. Gonnella, and M. Liepe, *J. Appl. Phys.* **121**, 043910 (2017).
<http://aip.scitation.org/doi/10.1063/1.4974909>
- A. Gurevich, *Phys. Rev. Lett.* **113**, 087001 (2014).
<http://link.aps.org/doi/10.1103/PhysRevLett.113.087001>
- P. N. Koufalidis, D. L. Hall, M. Liepe, and J. T. Maniscalco, arXiv:1612.08291 (2016).
- J. T. Maniscalco, F. Furuta, D. L. Hall, P. N. Koufalidis, M. Liepe, IPAC 2017.
<http://jacow.org/ipac2017/papers/wepva145.pdf>
- J. T. Maniscalco, M. Liepe, R. D. Porter, SRF 2017 pre-press (once available),
contribution THPB005 (2017).
- M. Martinello *et al.*, arXiv:1707.07582 (2017).
- H. T. Edwards *et al.*, SRF 2009.

This work supported under NSF Award No. PHY-1549132, the Center for Bright Beams,
and NSF Award No. PHY-1416318.





- Strong RF magnetic fields excite screening currents on superconducting surface which modify density of states of quasiparticles (unpaired electrons)
- Decreases R_s for sufficiently sharp gap peak
- Nonequilibrium effects further suppress R_s

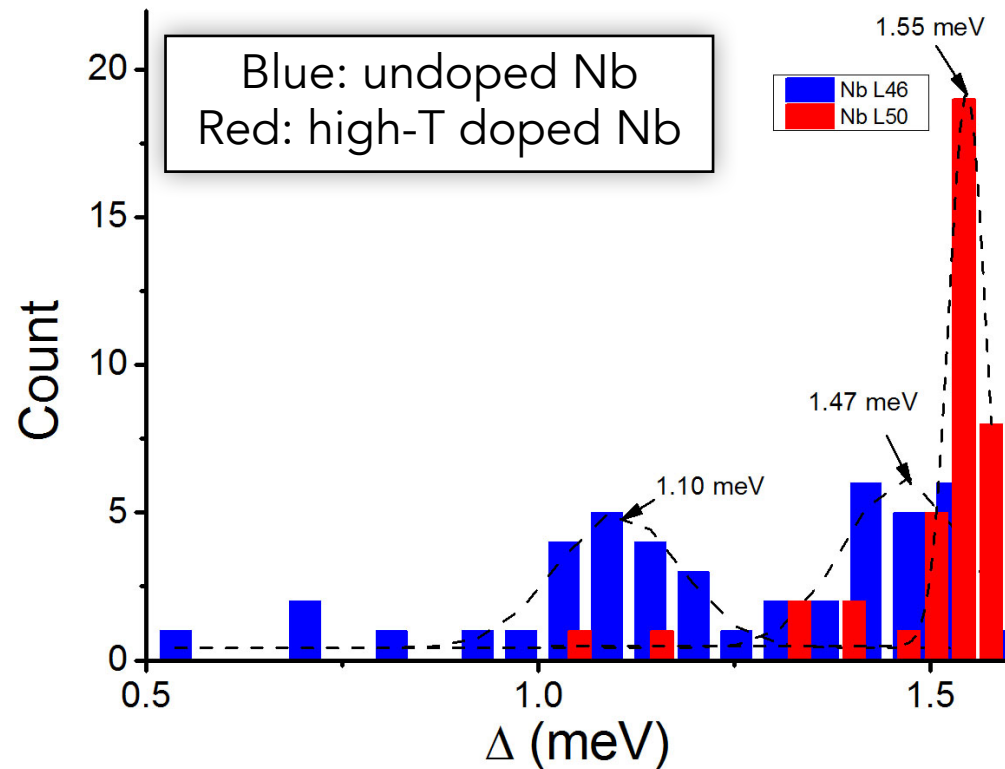


Reduction of Dissipative
Nonlinear Conductivity of
Superconductors
by Static and Microwave
Magnetic Fields

A. Gurevich, PRL **113**,
087001 (2014)

At left: Fig. 2, *ibid.*

- **Doping** connection: doping Nb sharpens gap peak?
 - Early results indicated more uniform energy gap on surface, but need more systematic data



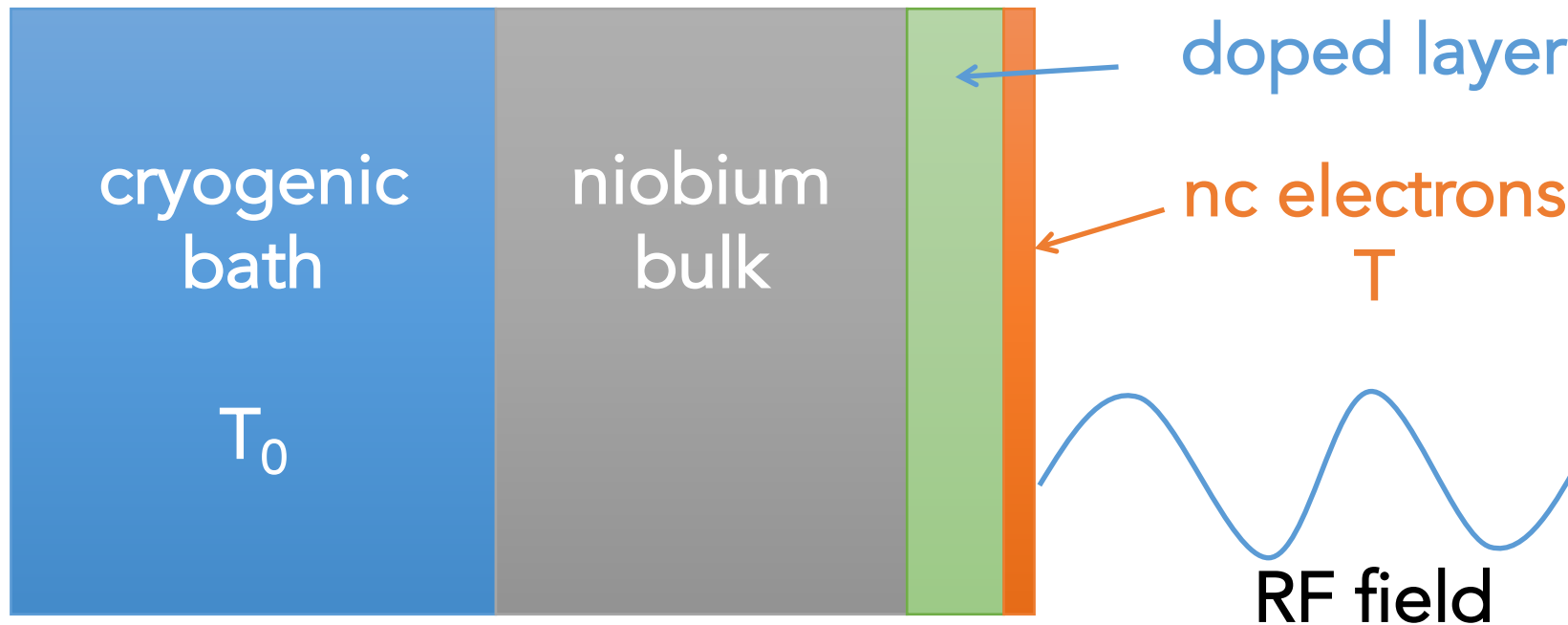
Effect of high-temperature heat treatments on the quality factor of a large-grain superconducting radio-frequency niobium cavity

P. Dhakal *et al.*, PRST-AB **16**, 042001 (2013)

At left: Fig. 16, *ibid.*

- Quasiparticle **overheating**

$$T - T_0 = \alpha' \frac{1}{2} H_a^2 R_{\text{BCS}}(H_a, T) = \alpha' \frac{P_{\text{diss}}}{\text{area}}$$



- Quasiparticle **overheating**

$$T - T_0 = \alpha' \frac{1}{2} H_a^2 R_{\text{BCS}}(H_a, T) = \alpha' \frac{P_{\text{diss}}}{\text{area}}$$

$$\alpha' = \left(\frac{1}{Y} + \frac{d}{\kappa} + \frac{1}{h_K} \right)$$

Y (e-phonon energy transfer)
dominates, can be
dependent on
mean free path

properties of
bulk, do not
change
with doping



$$R_s = R_0 + R_{BCS}$$

$T = T_{\text{electron}}$ = temperature of quasiparticles

T_0 = cryogenic bath temperature

α' = normalized overheating parameter

Y = electron-phonon energy transfer rate

κ = thermal conductivity

d = thickness of cavity wall

h_K = Kapitza interface conductance

P_{diss} = power dissipated in cavity walls





- Nitrogen-doped 1.3 GHz TESLA single-cell niobium cavities
 - Prepared with a range of electron mean free paths from 4 nm to over 200 nm
 - 100 μm vertical electropolish (VEP) "reset"
 - 800 $^{\circ}\text{C}$ in vacuum, 3 h, "outgassing"
 - 800-990 $^{\circ}\text{C}$ in 4-8 Pa (30-60 mTorr) N_2 , 5-30 min
 - 5-40 μm VEP to determine "doping level", quantified by electron mean free path (deeper etch reveals cleaner layer)
- Low-T doping at 120-160 $^{\circ}$ C
 - chemical reset and outgassing bake phase
 - 48 h bake with nitrogen gas, impurities at ppm level
 - 48-168 h anneal in vacuum

